

In re the Application of Rule 53(b) Divisional: MORIIZUMI, Kiyokazu et al.  
U.S Serial No. 09/705,897 (Parent)  
Preliminary Amendment

**Amendments to the Specification:**

**Please amend the specification by inserting after the title:**

This application is a **DIVISION** of prior application Serial No. 09/705,897 filed  
Patent No. 6,717,262

November 6, 2000

**Please amend the paragraph beginning at page 6, line 9, as follows:**

On the other hand, on the thin-film multilayer interconnect substrate D part 32 is mounted an LSI chip 34 "flipped" top-side down, by means of solder bumps 33 35 made of Pb-Sn or the like, and cooling fins 36 are mounted on the reverse side of the LSI chip 34 to dissipate the heat generated in the LSI.

**Please amend the paragraph beginning at page 16, line 29, as follows:**

Next, as shown in Fig. 7G, a W tungsten (W) film 18 with a maximum thickness of several thousand angstroms, for example, 3000 Å, is deposited by sputtering over the entire surface.

**Please amend the paragraph beginning at page 21, line 32, as follows:**

In each of the above embodiments, W tungsten (W) is used to form the film that acts as a stopper in the CMP process, but the material is not limited to W; the only requirement here is that the film be a metal film harder than the Ni electroplated pad to be polished, and even an insulating film may be used.